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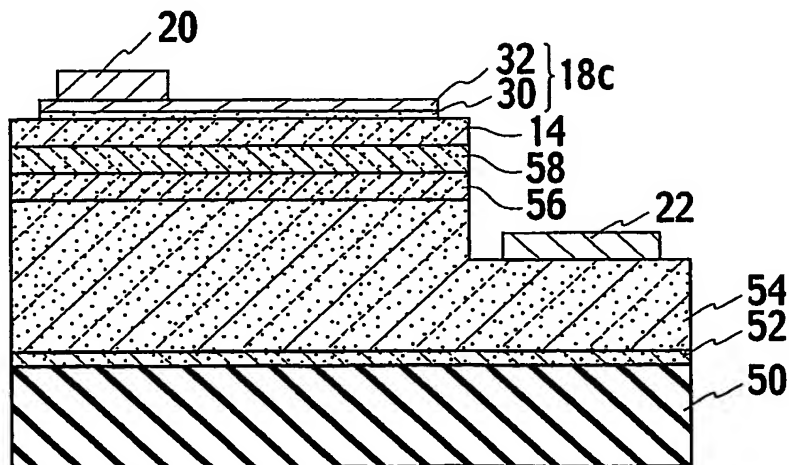
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FACTURING A SEMICONDUCTOR DEVICE



(57) Abstract: A semiconductor device includes a p-type nitride semiconductor layer (14); and a p-side electrode (18) including a  
palladium oxide film (30) connected to a surface of the nitride semiconductor layer (14).

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